

N-Channel 100 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) Max.	I _D (A)	Q _g (Typ.)
100	0.076 at V _{GS} = 10 V	g ^d	8.5
	0.096 at V _{GS} = 6 V	g ^d	

FEATURES

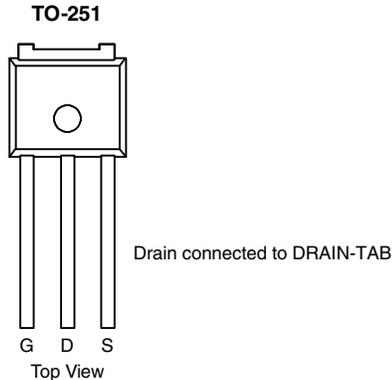
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC



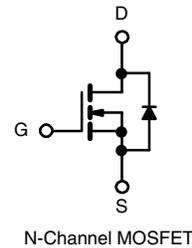
RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- DC/DC Converters
- Motor Control



Ordering Information
SUU09N10-76P-GE3 (Lead (Pb)-free and Halogen-free)



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	100	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	g ^d
		T _C = 70 °C	g ^d
Pulsed Drain Current (t = 300 μs)	I _{DM}	20	A
Avalanche Current	I _{AS}	18	
Single Avalanche Energy ^a	E _{AS}	16.2	mJ
Maximum Power Dissipation ^a	P _D	T _C = 25 °C	32.1 ^b
		T _A = 25 °C ^c	2.5
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	50	°C/W
Junction-to-Case (Drain)	R _{thJC}	3.9	

Notes:

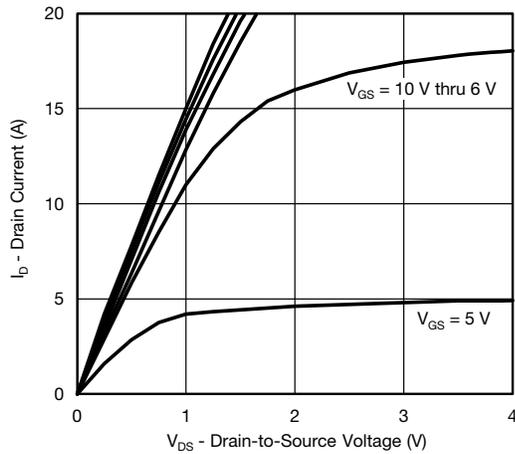
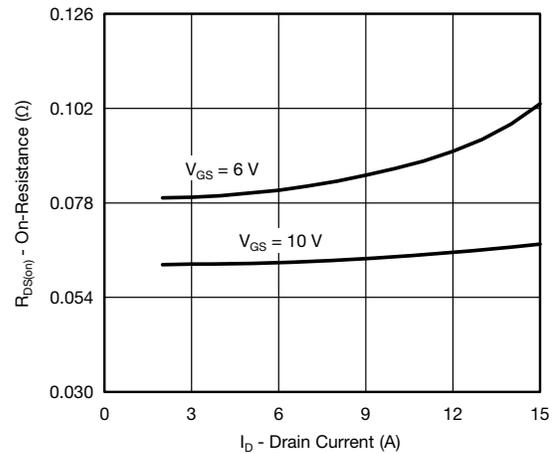
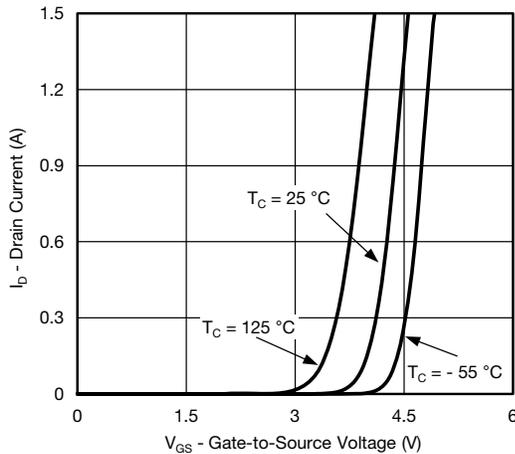
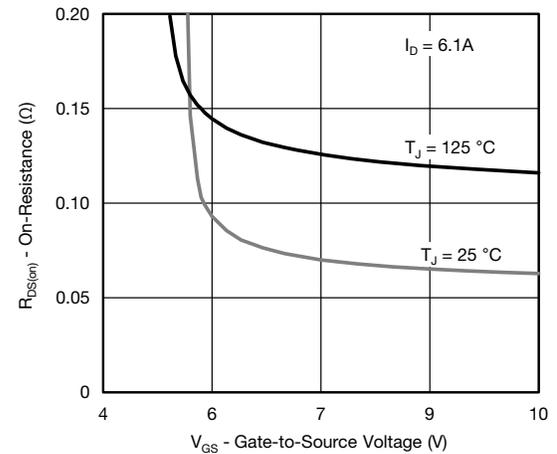
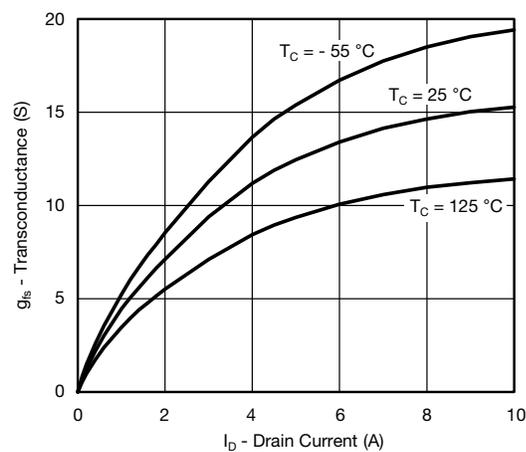
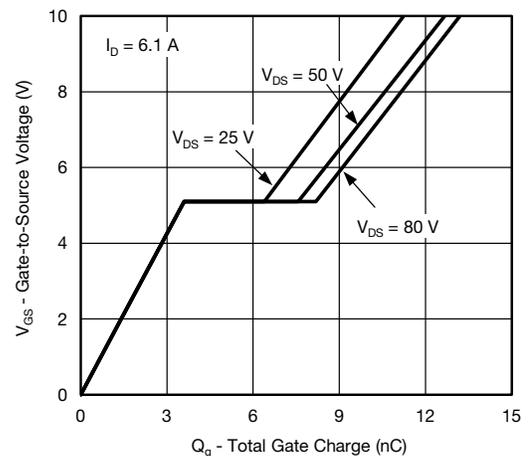
- Duty cycle ≤ 1 %.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).
- Package limited

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	100			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.5		4	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 250	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			50	
		$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$			250	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$	15			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 6.1\text{ A}$		0.063	0.076	Ω
		$V_{GS} = 6\text{ V}, I_D = 5.4\text{ A}$		0.080	0.096	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -20\text{ V}, I_D = 6.1\text{ A}$		13		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 50\text{ V}, f = 1\text{ MHz}$		505		μF
Output Capacitance	C_{oss}			71		
Reverse Transfer Capacitance	C_{rss}			35		
Total Gate Charge ^c	Q_g	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 6.1\text{ A}$		12.7	19.1	nC
		$V_{DS} = 50\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 6.1\text{ A}$		8.5	12.8	
Q_{gs}			3.6			
Q_{gd}			4			
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.2	0.9	1.8	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = 50\text{ V}, R_L = 10.2\text{ }\Omega$ $I_D \cong 4.9\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		7	14	ns
Rise Time ^c	t_r			11	20	
Turn-Off Delay Time ^c	$t_{d(off)}$			11	20	
Fall Time ^c	t_f			6	12	
Drain-Source Body Diode Ratings and Characteristics $T_C = 25\text{ }^\circ\text{C}^b$						
Continuous Current	I_S				9	A
Pulsed Current	I_{SM}				20	
Forward Voltage ^a	V_{SD}	$I_F = 4.9\text{ A}, V_{GS} = 0\text{ V}$		0.82	1.5	V
Reverse Recovery Time	t_{rr}	$I_F = 4.9\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		36	53	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			2.7	4.1	A
Reverse Recovery Charge	Q_{rr}			46	69	nC

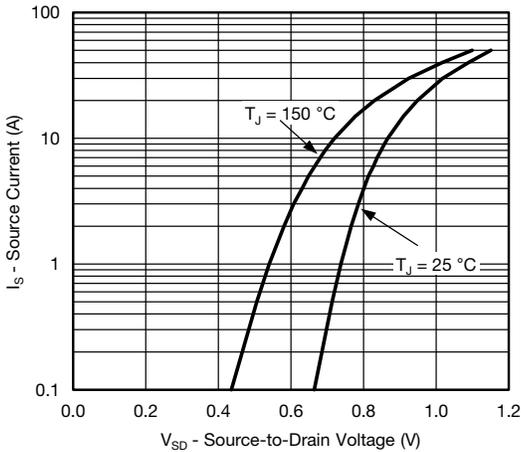
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

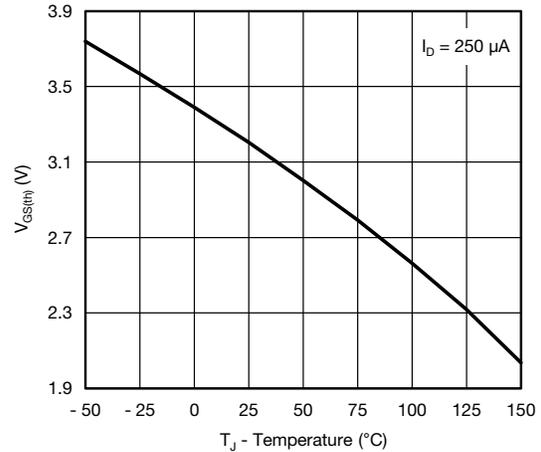
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

On-Resistance vs. Drain Current

Transfer Characteristics

On-Resistance vs. Gate-to-Source Voltage

Transconductance

Gate Charge

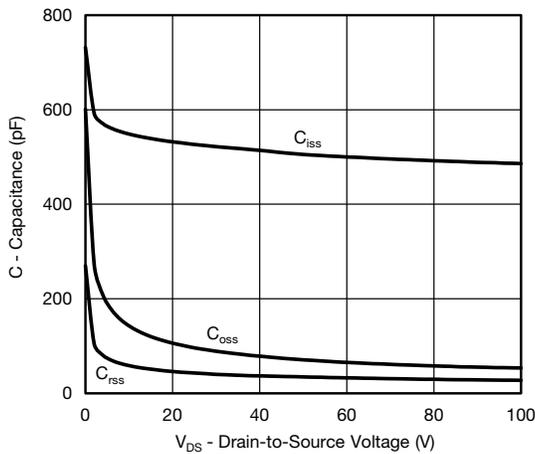
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



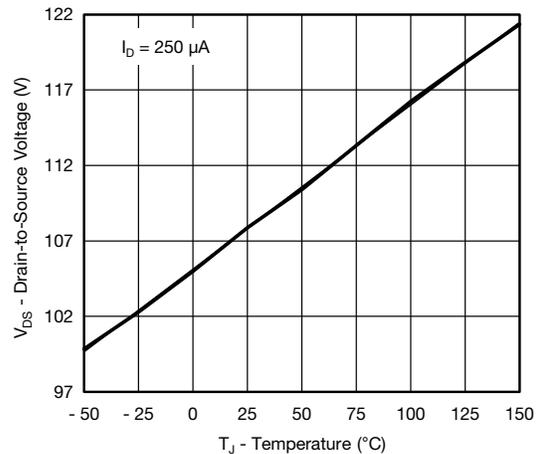
Source-Drain Diode Forward Voltage



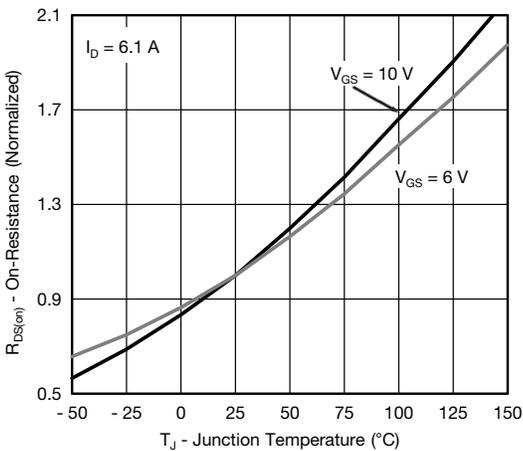
Threshold Voltage



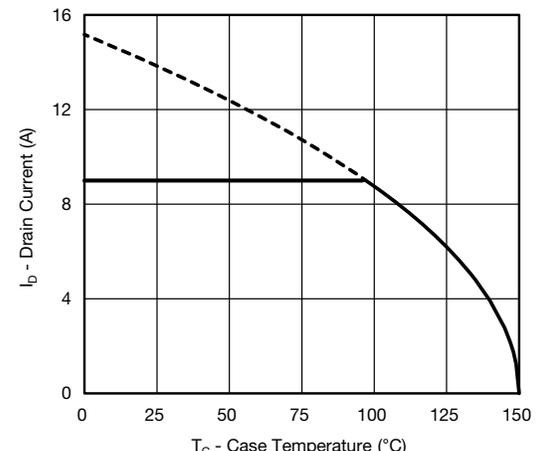
Capacitance



Drain Source Breakdown vs. Junction Temperature

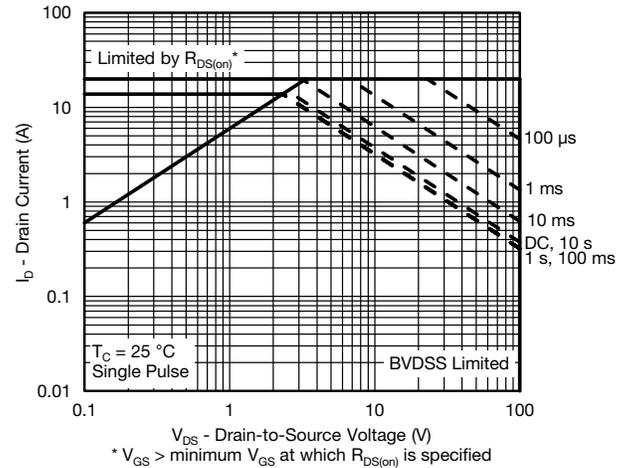
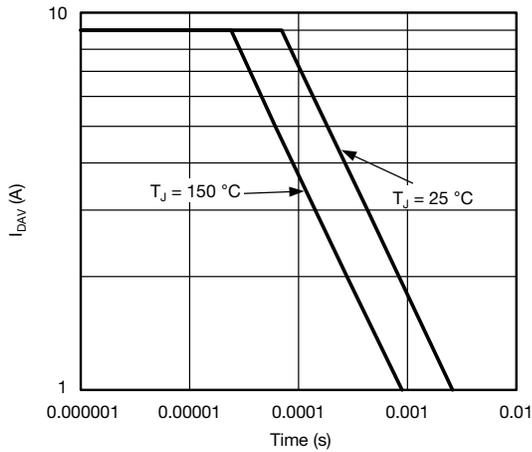


On-Resistance vs. Junction Temperature



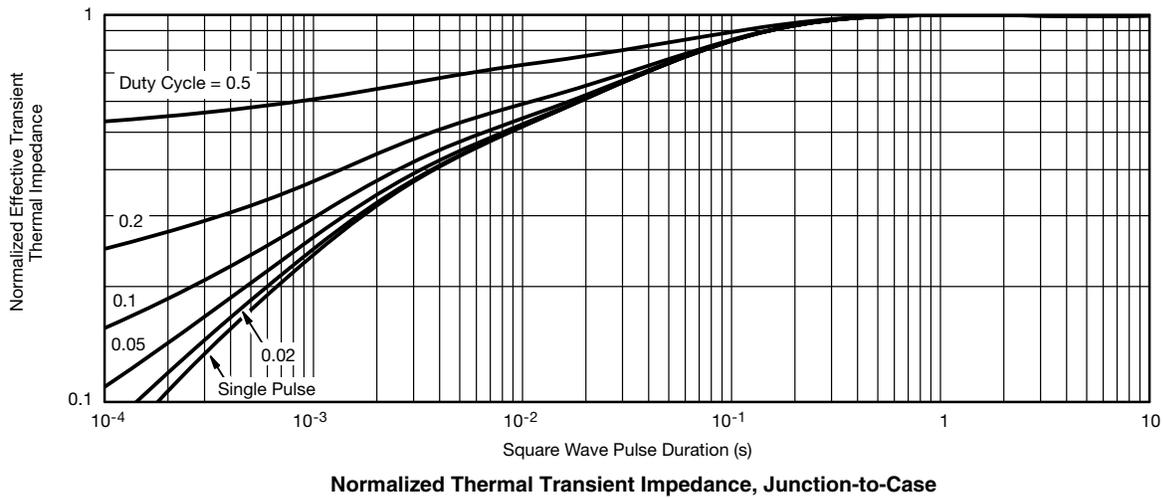
Current Derating

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Single Pulse Avalanche Current Capability vs. Time

Safe Operating Area

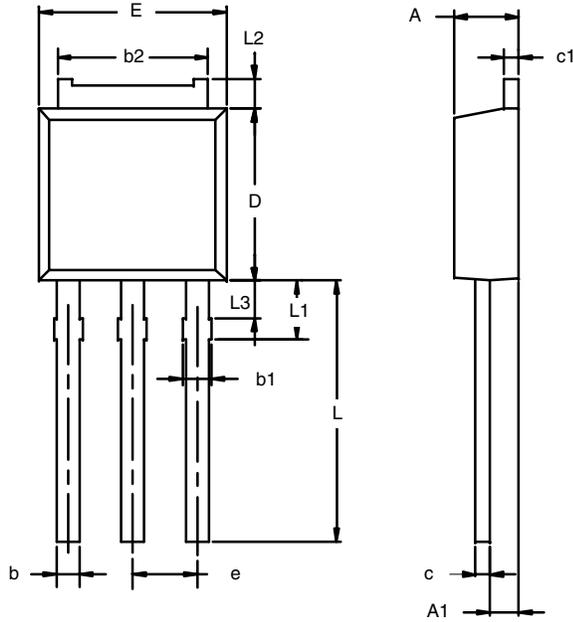


Normalized Thermal Transient Impedance, Junction-to-Case

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TO-251AA (IPAK)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	2.21	2.38	0.087	0.094
A1	0.89	1.14	0.035	0.045
b	0.71	0.89	0.028	0.035
b1	0.76	1.14	0.030	0.045
b2	5.23	5.43	0.206	0.214
C	0.46	0.58	0.018	0.023
C1	0.46	0.58	0.018	0.023
D	5.97	6.22	0.235	0.245
E	6.48	6.73	0.255	0.265
e	2.28 BSC		0.090 BSC	
L	8.89	9.53	0.350	0.375
L1	1.91	2.28	0.075	0.090
L2	0.89	1.27	0.035	0.050
L3	1.15	1.52	0.045	0.060
ECN: T13-0362-Rev. F, 03-Jun-13				
DWG: 5346				

Note

- Dimension L3 is for reference only.



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